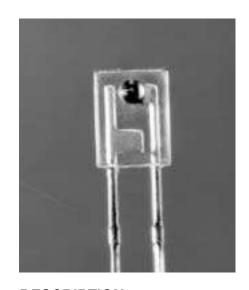
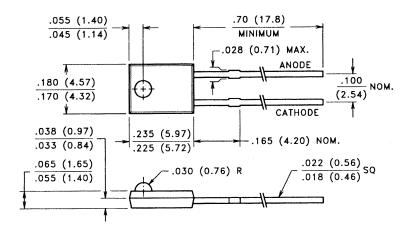
GaAlAs Infrared Emitting Diodes

Molded Lateral Package — 880 nm

VTE7172H, 7173H



PACKAGE DIMENSIONS inch (mm)



DESCRIPTION

CASE 7 LATERAL CHIP SIZE: .011" x .011"

These side-looking packages are designed for use in PC board mounted interrupt detectors. The package is transfer molded plastic and contains a high efficiency, 880 nm, GaAlAs IRED die.

RoHS Compliant

Pb

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 85°C	Maximum Reverse Current @ V _R = 5V:	10 μA
Continuous Power Dissipation:	100 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	1.82 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF
Maximum Continuous Current:	50 mA	Response Time @ I _F = 20 mA	·
Derate above 30°C:	0.91 mA/°C	Rise: 1.0 µs Fall: 1.0 µs	
Peak Forward Current, 10 µs, 100 pps:	2.5 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	8%/°C	(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

		Output						Forward Drop		Half Dawer Daam
Part Number	Irrad	Irradiance			Total Power	Test Current	V _F		Half Power Beam Angle	
E _e		е	Condition		I _e	Po	I _{FT}	@ I _{FT}		$\theta_{1/2}$
	mW/cm ²		distance	Diameter	mW/sr	mW	mA	Volts		Tun
	Min.	Тур.	mm	mm	Min.	Тур.	(Pulsed)	Тур.	Max.	Тур.
VTE7172H	0.4	0.6	16.7	4.6	1.1	2.5	20	1.3	1.8	±25°
VTE7173H	0.6	0.8	16.7	4.6	1.7	5.0	20	1.3	1.8	±25°

■ Refer to General Product Notes, page 2.